

# S-5742 B Series

# 125°C OPERATION HIGH-WITHSTAND VOLTAGE HIGH-SPEED BIPOLAR HALL EFFECT LATCH IC

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Rev.2.1\_02

This IC, developed by CMOS technology, is a bipolar Hall effect latch IC with high-withstand voltage, high-speed detection and high-accuracy magnetic characteristics.

The output voltage changes when this IC detects the intensity level of magnetic flux density and a polarity change. Using this IC with a magnet makes it possible to detect the rotation status in various devices.

This IC includes an output current limit circuit.

This IC is available in various systems by using the insertion TO-92S package.

Due to its high-accuracy magnetic characteristics, this IC can make operation's dispersion in the system combined with magnet smaller.

ABLIC Inc. offers a "magnetic simulation service" that provides the ideal combination of magnets and our Hall ICs for customer systems. Our magnetism simulation service will reduce prototype production, development period and development costs. In addition, it will contribute to optimization of parts to realize high cost performance. For more information regarding our magnetism simulation service, contact our sales office.

# Features

- Pole detection:
- Output logic<sup>\*1</sup>:
- Output form<sup>\*1</sup>:
- Magnetic sensitivity<sup>\*1</sup>:
- Chopping frequency:
- Output delay time:
- Power supply voltage range:
- Built-in regulator
- Built-in output current limit circuit
- Operation temperature range:
- Lead-free (Sn 100%), halogen-free

\*1. The option can be selected

# Applications

- Home appliance
- DC brushless motor
- Housing equipment
- Industrial equipment

# Packages

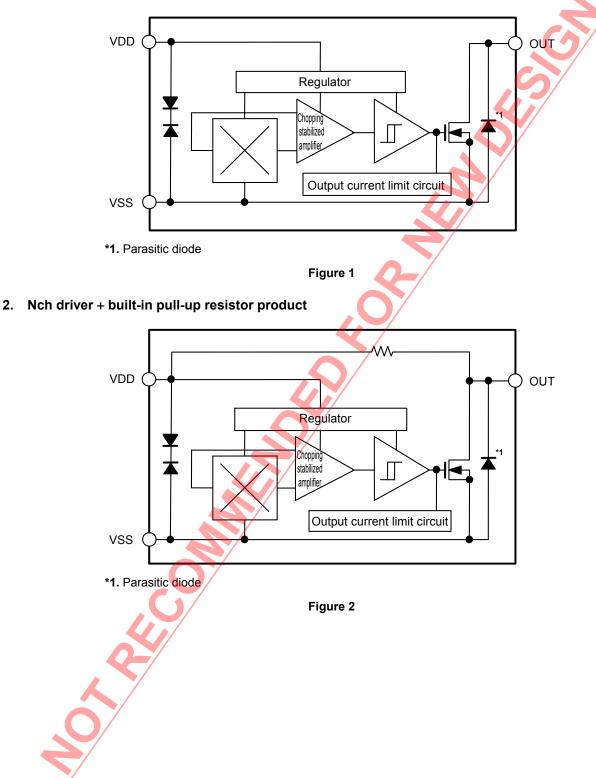
- TO-92S (Straight)
- TO-92S (Forming)

Bipolar latch  $V_{OUT}$  = "L" at S pole detection  $V_{OUT}$  = "H" at S pole detection Nch open-drain output Nch driver + built-in pull-up resistor  $B_{OP}$  = 1.8 mT typ.  $B_{OP}$  = 3.0 mT typ.  $B_{OP}$  = 6.0 mT typ.  $f_{C}$  = 500 kHz typ.  $t_{D}$  = 8.0 µs typ.  $V_{DD}$  = 3.5 V to 26.0 V

Ta = -40°C to +125°C

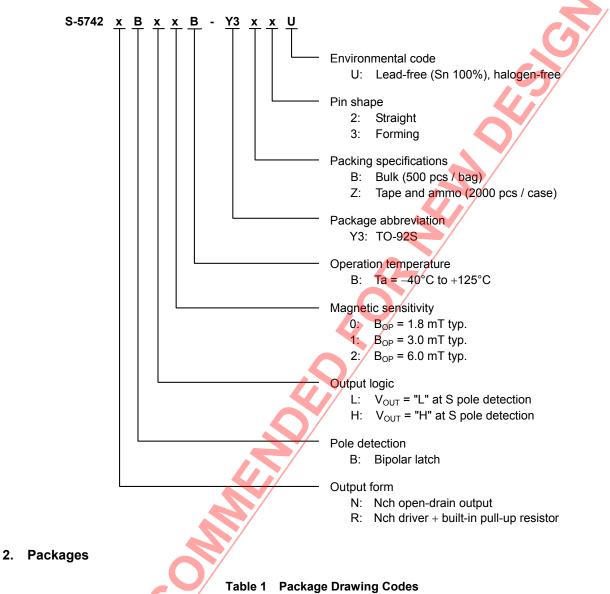
# ■ Block Diagrams

1. Nch open-drain output product



### Product Name Structure

1. Product name



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	Package Name	Dimension	Таре	Ammo Packing
	TO 025 (Straight) Bulk	YB003-A-P-SD	_	_
	TO-92S (Straight) Tape and amm		YC003-A-C-SD	YC003-A-Z-SD
	TO 020 (Forming) Bulk		_	-
	TO-92S (Forming) Tape and amm	o YB003-B-P-SD	YC003-B-C-SD	YC003-B-Z-SD

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### 3. Product name list

### 3.1 TO-92S (Straight)

	Table :	2		
Product Name <sup>*1</sup>	Output Form	Pole Detection	Output logic	Magnetic Sensitivity (B <sub>OP</sub> )
S-5742NBL0B-Y3n2U	Nch open-drain output	Bipolar latch	V <sub>OUT</sub> = "L" at S pole detection	1.8 mT typ.
S-5742NBL1B-Y3n2U	Nch open-drain output	Bipolar latch	V <sub>OUT</sub> = "L" at S pole detection	3.0 mT typ.
S-5742NBL2B-Y3n2U	Nch open-drain output	Bipolar latch	V <sub>OUT</sub> = "L" at S pole detection	6.0 mT typ.
S-5742NBH0B-Y3n2U	Nch open-drain output	Bipolar latch	V <sub>OUT</sub> = "H" at S pole detection	1.8 mT typ.
S-5742NBH1B-Y3n2U	Nch open-drain output	Bipolar latch	V <sub>OUT</sub> = "H" at S pole detection	3.0 mT typ.
S-5742NBH2B-Y3n2U	Nch open-drain output	Bipolar latch	V <sub>OUT</sub> = "H" at S pole detection	6.0 mT typ.
S-5742RBL0B-Y3n2U	Nch driver + built-in pull-up resistor	Bipolar latch	V <sub>OUT</sub> = "L" at S pole detection	1.8 mT typ.
S-5742RBL1B-Y3n2U	Nch driver + built-in pull-up resistor	Bipolar latch	V <sub>OUT</sub> = "L" at S pole detection	3.0 mT typ.
S-5742RBL2B-Y3n2U	Nch driver + built-in pull-up resistor	Bipolar latch	V <sub>OUT</sub> = "L" at S pole detection	6.0 mT typ.
S-5742RBH0B-Y3n2U	Nch driver + built-in pull-up resistor	Bipolar latch	Vout = "H" at S pole detection	1.8 mT typ.
S-5742RBH1B-Y3n2U	Nch driver + built-in pull-up resistor	Bipolar latch	Vour = "H" at S pole detection	3.0 mT typ.
S-5742RBH2B-Y3n2U	Nch driver + built-in pull-up resistor	Bipolar latch	$V_{OUT}$ = "H" at S pole detection	6.0 mT typ.

\*1. "n" changes according to the packing specification as follows. B: Bulk, Z: Tape and ammo

Remark Please contact our sales office for products other than the above.

### 3.2 TO-92S (Forming)

### Table 3

Product Name*1	Output Form	Pole Detection	Output logic	Magnetic Sensitivity (B <sub>OP</sub> )
S-5742NBL1B-Y3n3U	Nch open-drain output	Bipolar latch	V <sub>OUT</sub> = "L" at S pole detection	3.0 mT typ.
S-5742NBL2B-Y3n3U	Nch open-drain output	Bipolar latch	V <sub>OUT</sub> = "L" at S pole detection	6.0 mT typ.
S-5742RBH1B-Y3n3U	Nch driver + built-in pull-up resistor	Bipolar latch	V <sub>OUT</sub> = "H" at S pole detection	3.0 mT typ.

\*1. "n" changes according to the packing specification as follows. B: Bulk, Z: Tape and ammo

Remark Please contact our sales office for products other than the above.

# Pin Configuration

1. TO-92S



Table 4								
Pin No.	Symbol	Description						
1	VDD	Power supply pin						
2	VSS	GND pin						
3	OUT	Output pin						

Figure 3

# Absolute Maximum Ratings

	Table 5			
			(Ta = +25°C unless otherwise sp	ecified)
	Item	Symbol	Absolute Maximum Rating	Unit
Power supply vo	Itage	V <sub>DD</sub>	V <sub>SS</sub> – 0.3 to V <sub>SS</sub> + 28.0	V
Output current		I <sub>OUT</sub>	20	mA
Output voltage	Nch open-drain output product	V	$V_{SS} - 0.3$ to $V_{SS} + 28.0$	V
Output voltage	Nch driver + built-in pull-up resistor product	- V <sub>OUT</sub>	$V_{SS} - 0.3$ to $V_{DD} + 0.3$	V
Operation ambie	nt temperature	T <sub>opr</sub>	-40 to +125	°C
Storage tempera	ture	T <sub>stg</sub>	-40 to +150	°C

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

# Thermal Resistance Value

		Table 6					
Item	Symbol	Con	dition	Min.	Тур.	Max.	Unit
Junction-to-ambient thermal resistance	$\theta_{JA}$	TO-92S		-	153 <sup>*1</sup>	_	°C/W

\*1. When not mounted on board

**Remark** Refer to "**■ Power Dissipation**" for details.

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# Electrical Characteristics

		<b>Table 7</b> (Ta = +25°C, V <sub>DD</sub> = 12.0 V, V	√ <sub>SS</sub> = 0	V unles	s other	wise sp	ecified)
Item	Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Power supply voltage	V <sub>DD</sub>	_	3.5	12.0	26.0	V	-
Current consumption		Nch open-drain output product Average value	-	3.0	4.0	mA	1
Current consumption	I <sub>DD</sub>	Nch driver + built-in pull-up resistor product Average value, V <sub>OUT</sub> = "H"		3.0	4.0	mA	1
Output voltage		Nch open-drain output product Output transistor Nch, V <sub>OUT</sub> = "L", I <sub>OUT</sub> = 10 mA	-	-	0.4	V	2
Output voltage	V <sub>OUT</sub>	Nch driver + built-in pull-up resistor product Output transistor Nch, $V_{OUT}$ = "L", $I_{OUT}$ = 10 mA	-	_	0.5	V	2
Output drop voltage	V <sub>D</sub>	Nch driver + built-in pull-up resistor product $V_{OUT} = "H", V_D = V_{DD} - V_{OUT}$	-	_	20	mV	2
Leakage current	$I_{LEAK}$	Nch open-drain output product Output transistor Nch, $V_{OUT}$ = "H" = 26.0 V	-	_	10	μA	3
Output limit current	I <sub>OM</sub>	V <sub>OUT</sub> = 12.0 V	22	-	70	mA	3
Output delay time	t <sub>D</sub>	-	-	8.0	-	μs	_
Chopping frequency	f <sub>C</sub>	- , 0/	-	500	-	kHz	-
Start up time	t <sub>PON</sub>	-	-	20	-	μS	4
Output rise time	t_	Nch open-drain output product C = 20 pF, R = 820 $\Omega$	-	-	2.0	μS	5
Output rise time	t <sub>R</sub>	Nch driver + built-in pull-up resistor product C = 20 pF	-	-	6.0	μS	5
Output fall time	t <sub>F</sub>	C = 20 pF, R = 820 Ω	_	_	2.0	μS	5
Pull-up resistor	RL	Nch driver + built-in pull-up resistor product	7	10	13	kΩ	-

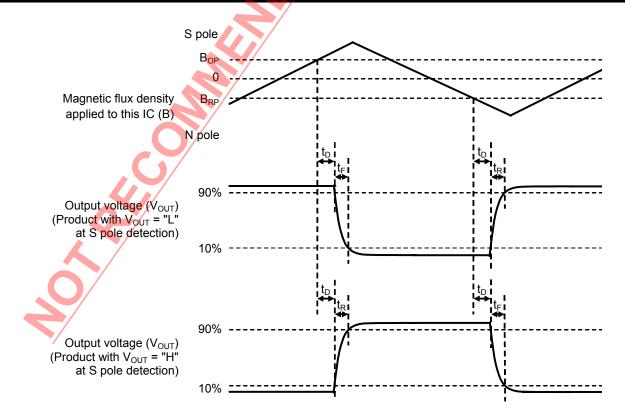


Figure 4 Operation Timing

### Magnetic Characteristics

### 1. Product with $B_{OP} = 1.8 \text{ mT typ.}$

			Table 8					
			(Ta = +25	°C, V <sub>DD</sub> = ′	12.0 V, V <sub>SS</sub>	= 0 V unle	ss other	wise specified)
Item	า	Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Operation point <sup>*1</sup>	S pole	B <sub>OP</sub>	-	0.3	1.8	3.3	mT	4
Release point <sup>*2</sup>	N pole	B <sub>RP</sub>	_	-3.3	-1.8	-0.3	mТ	4
Hysteresis width*3		B <sub>HYS</sub>	$B_{HYS} = B_{OP} - B_{RP}$	_	3.6	4	mT	4

### 2. Product with $B_{OP} = 3.0 \text{ mT typ.}$

#### Table 9

			(Ta = +25)	°C, V <sub>DD</sub> = 1	12.0 V, V <sub>SS</sub>	= 0 V unle	ss other	wise specified)
Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Operation point <sup>*1</sup>	S pole	B <sub>OP</sub>	_	1.5 💧	3.0	4.5	mT	4
Release point*2	N pole	B <sub>RP</sub>	_	-4.5	-3.0	-1.5	mT	4
Hysteresis width*3		B <sub>HYS</sub>	$B_{HYS} = B_{OP} - B_{RP}$	1	6.0		mT	4

3. Product with  $B_{OP} = 6.0 \text{ mT typ.}$ 

### Table 10

			(Ta = +25	<sup>™</sup> C, V <sub>DD</sub> = 1	12.0 V, V <sub>SS</sub>	= 0 V unle	ess other	wise specified)
Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Operation point <sup>*1</sup>	S pole	B <sub>OP</sub>	-	3.0	6.0	9.0	mT	4
Release point <sup>*2</sup>	N pole	B <sub>RP</sub>		-9.0	-6.0	-3.0	mT	4
Hysteresis width*3		B <sub>HYS</sub>	$B_{HYS} = B_{OP} - B_{RP}$	_	12.0	Ι	mT	4

**\*1.** B<sub>OP</sub>: Operation point

 $B_{OP}$  is the value of magnetic flux density when the output voltage ( $V_{OUT}$ ) changes after the magnetic flux density applied to this IC by the magnet (S pole) is increased (by moving the magnet closer).

V<sub>OUT</sub> retains the status until a magnetic flux density of the N pole higher than B<sub>RP</sub> is applied.

**\*2.** B<sub>RP</sub>: Release point

 $B_{RP}$  is the value of magnetic flux density when the output voltage (V<sub>OUT</sub>) changes after the magnetic flux density applied to this IC by the magnet (N pole) is increased (by moving the magnet closer).

V<sub>OUT</sub> retains the status until a magnetic flux density of the S pole higher than B<sub>OP</sub> is applied.

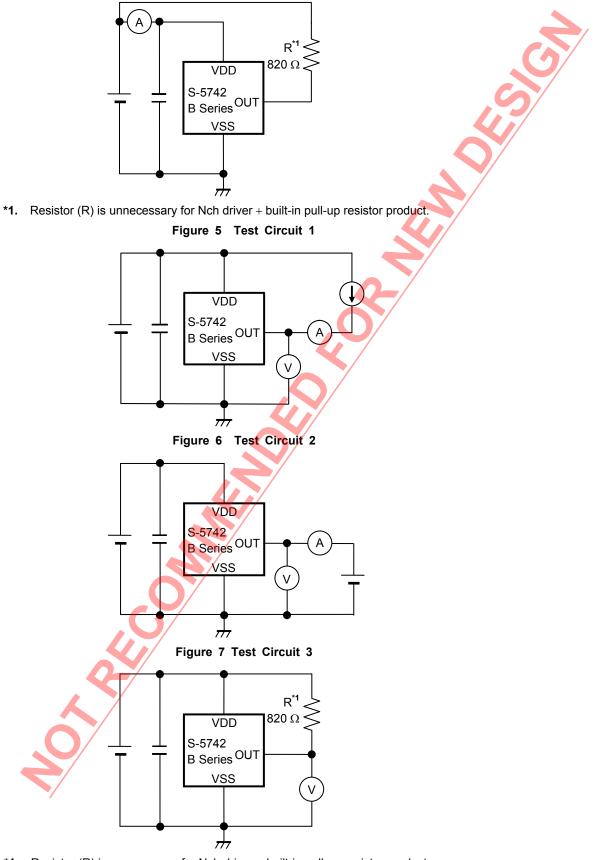
**\*3.** B<sub>HYS</sub>: Hysteresis width

 $B_{HYS}$  is the difference of magnetic flux density between  $B_{OP}$  and  $B_{RP}$ .

Remark The unit of magnetic flux density mT can be converted by using the formula 1 mT = 10 Gauss.

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# Test Circuits

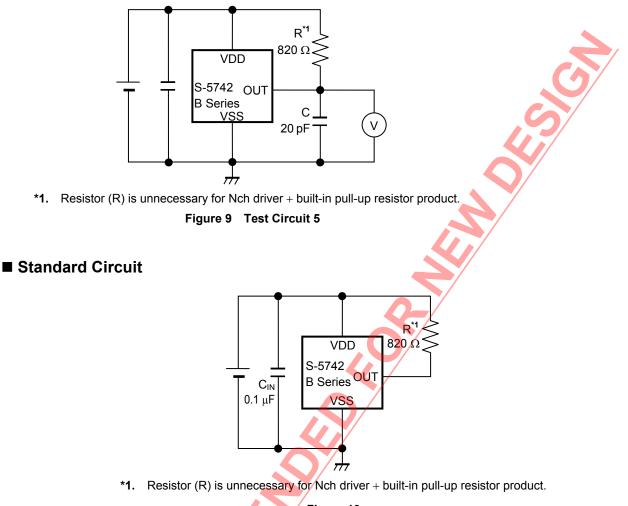


\*1. Resistor (R) is unnecessary for Nch driver + built-in pull-up resistor product.

Figure 8 Test Circuit 4

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# 125°C OPERATION HIGH-WITHSTAND VOLTAGE HIGH-SPEED BIPOLAR HALL EFFECT LATCH IC Rev.2.1\_02 S-5742 B Series



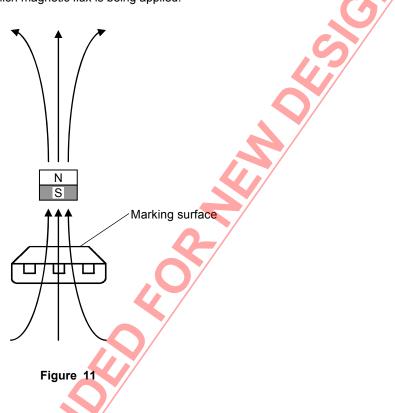
- Figure 10
- Caution The above connection diagram and constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.

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# Operation

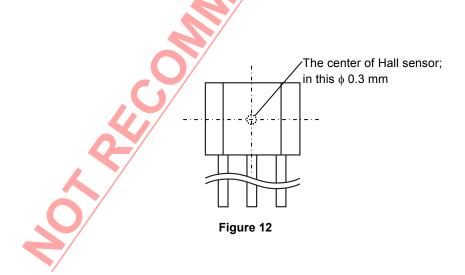
### 1. Direction of applied magnetic flux

This IC detects the magnetic flux density which is vertical to the marking surface. **Figure 11** shows the direction in which magnetic flux is being applied.



### 2. Position of Hall sensor

Figure 12 shows the position of Hall sensor. The center of this Hall sensor is located in the area indicated by a circle, which is in the center of a package as described below.

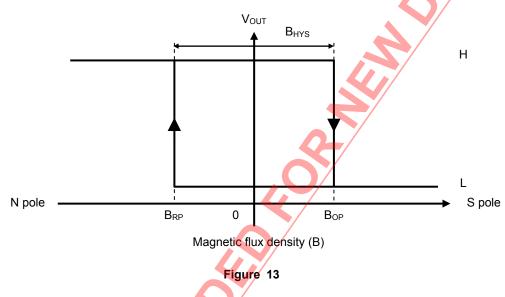


### 3. Basic operation

This IC changes the output voltage (V<sub>OUT</sub>) according to the level of the magnetic flux density and a polarity change (N pole or S pole) applied by a magnet.

#### 3. 1 Product with V<sub>OUT</sub> = "L" at S pole detection

When the magnetic flux density of the S pole perpendicular to the marking surface exceeds the operation point  $(B_{OP})$  after the S pole of a magnet is moved closer to the marking surface of this IC,  $V_{OUT}$  changes from "H" to "L". When the N pole of a magnet is moved closer to the marking surface of this IC and the magnetic flux density of the N pole is higher than the release point (B<sub>RP</sub>),  $V_{OUT}$  changes from "L" to "H". In case of B<sub>RP</sub> < B < B<sub>OP</sub>,  $V_{OUT}$  retains the status. **Figure 13** shows the relationship between the magnetic flux density and  $V_{OUT}$ .



### 3. 2 Product with V<sub>OUT</sub> = "H" at S pole detection

When the magnetic flux density of the S pole perpendicular to the marking surface exceeds  $B_{OP}$  after the S pole of a magnet is moved closer to the marking surface of this IC,  $V_{OUT}$  changes from "L" to "H". When the N pole of a magnet is moved closer to the marking surface of this IC and the magnetic flux density of the N pole is higher than  $B_{RP}$ ,  $V_{OUT}$  changes from "H" to "L". In case of  $B_{RP} < B < B_{OP}$ ,  $V_{OUT}$  retains the status. **Figure 14** shows the relationship between the magnetic flux density and  $V_{OUT}$ .

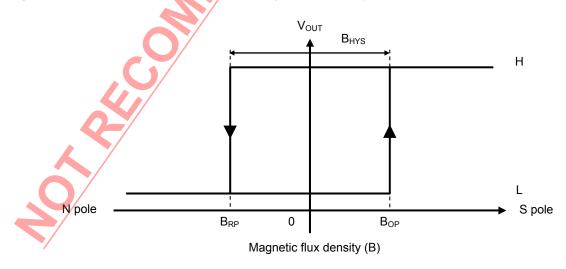


Figure 14

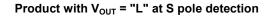
### 4. Timing chart

Figure 15 shows the operation timing at power-on.

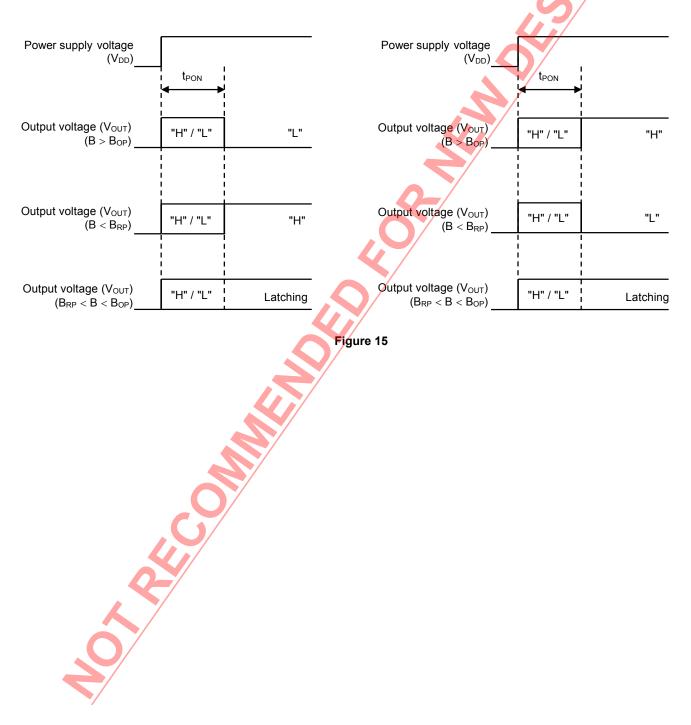
The initial output voltage at rising of power supply voltage ( $V_{DD}$ ) is either "H" or "L".

In case of B > B<sub>OP</sub> (operation point) or B < B<sub>RP</sub> (release point) at the time when the start up time ( $t_{PON}$ ) is passed after rising of V<sub>DD</sub>, this IC outputs V<sub>OUT</sub> according to the applied magnetic flux density.

In case of  $B_{RP} < B < B_{OP}$  at the time when  $t_{PON}$  is passed after rising of  $V_{DD}$ , this IC maintains the initial output voltage.



### Product with V<sub>OUT</sub> = "H" at S pole detection



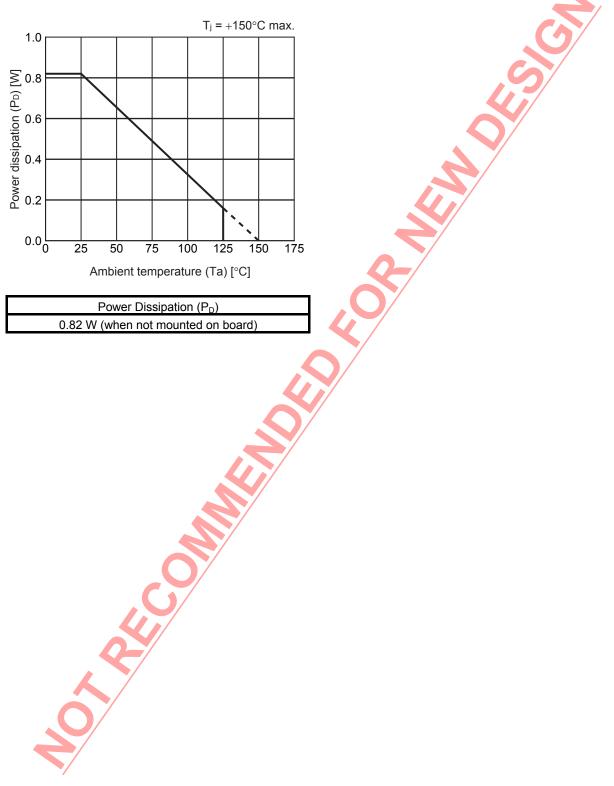
### Precautions

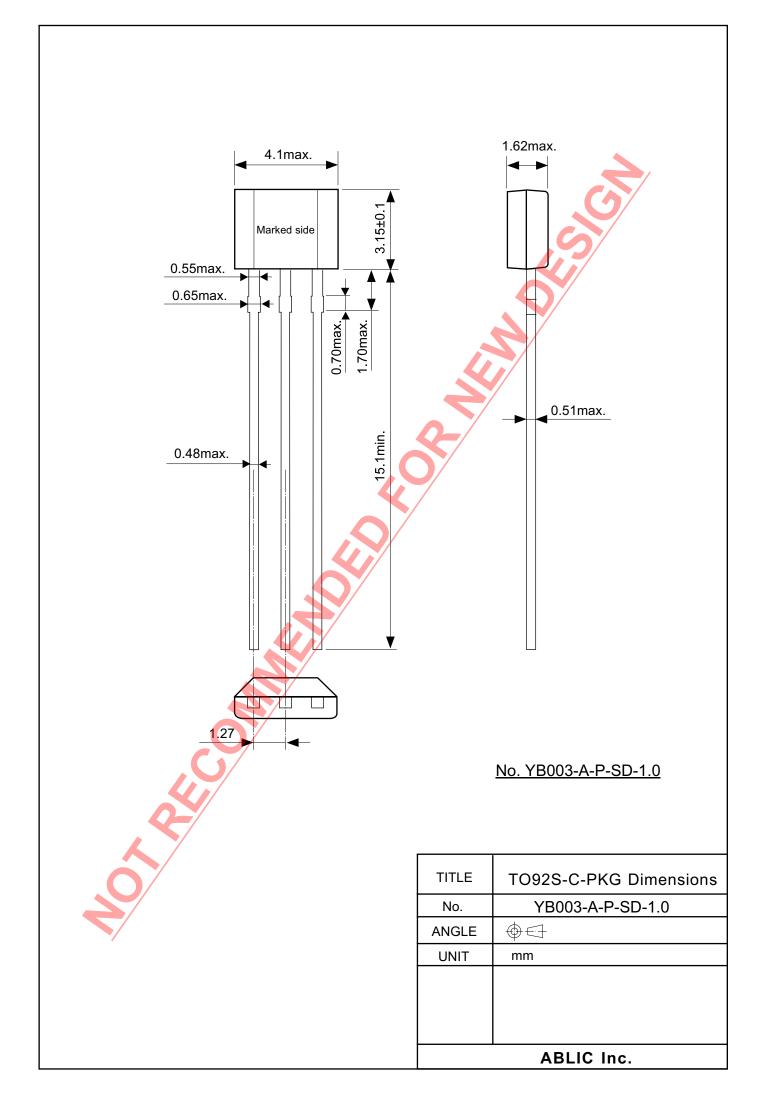
- If the impedance of the power supply is high, the IC may malfunction due to a supply voltage drop caused by feedthrough current. Take care with the pattern wiring to ensure that the impedance of the power supply is low.
- Note that the IC may malfunction if the power supply voltage rapidly changes. When the IC is used under the environment where the power supply voltage rapidly changes, it is recommended to judge the output voltage of the IC by reading it multiple times.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- Although this IC has a built-in output current limit circuit, it may suffer physical damage such as product deterioration under the environment where the absolute maximum ratings are exceeded.
- The application conditions for the power supply voltage, the pull-up voltage, and the pull-up resistor should not exceed the power dissipation.
- Large stress on this IC may affect on the magnetic characteristics. Avoid large stress which is caused by the handling during or after mounting the IC on a board.
- ABLIC Inc. claims no responsibility for any disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

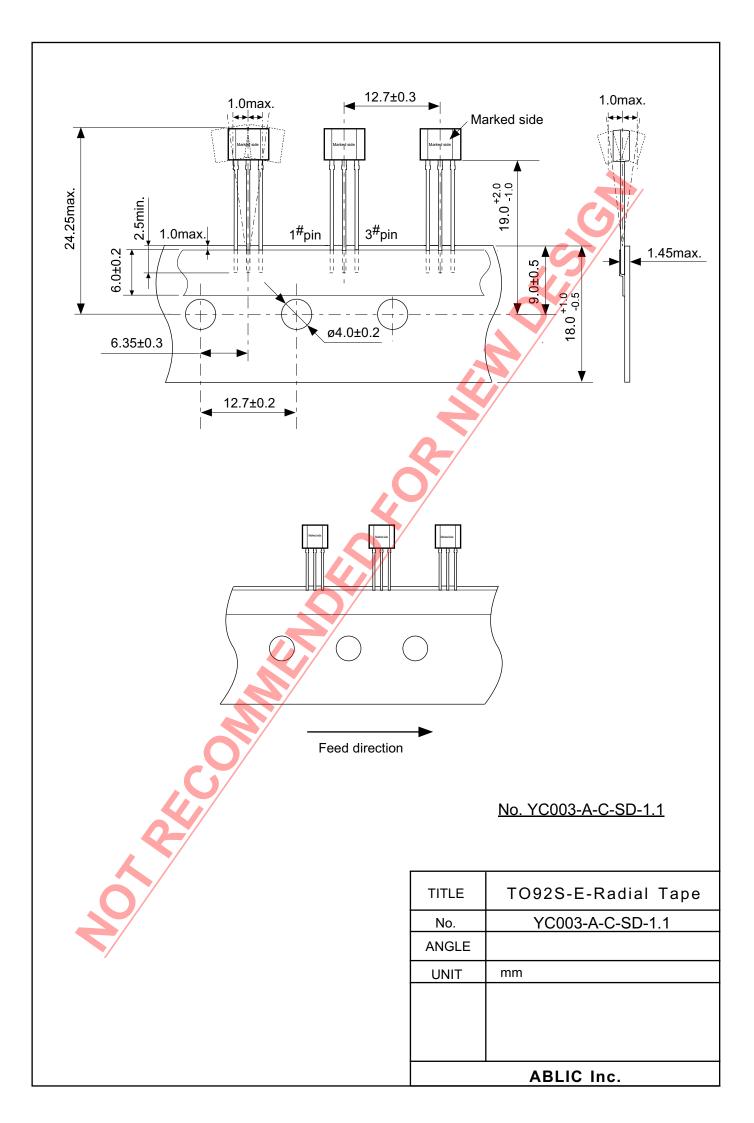
# 125°C OPERATION HIGH-WITHSTAND VOLTAGE HIGH-SPEED BIPOLAR HALL EFFECT LATCH IC S-5742 B Series Rev.2.1\_02

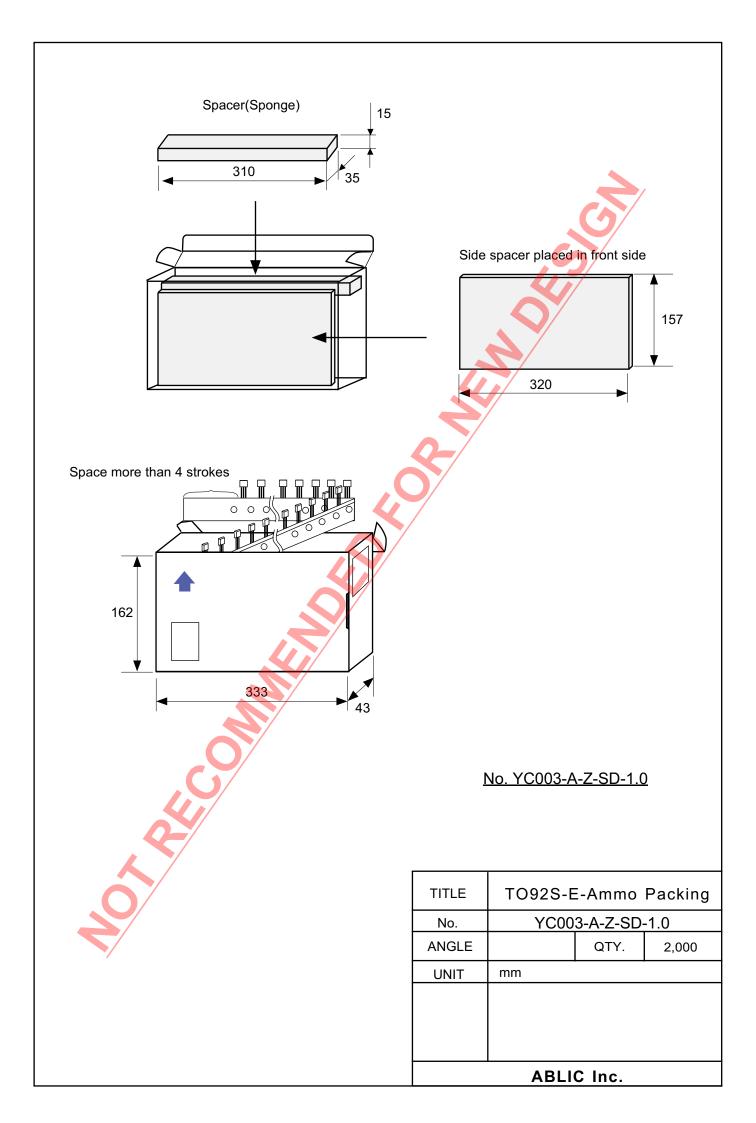
# Power Dissipation

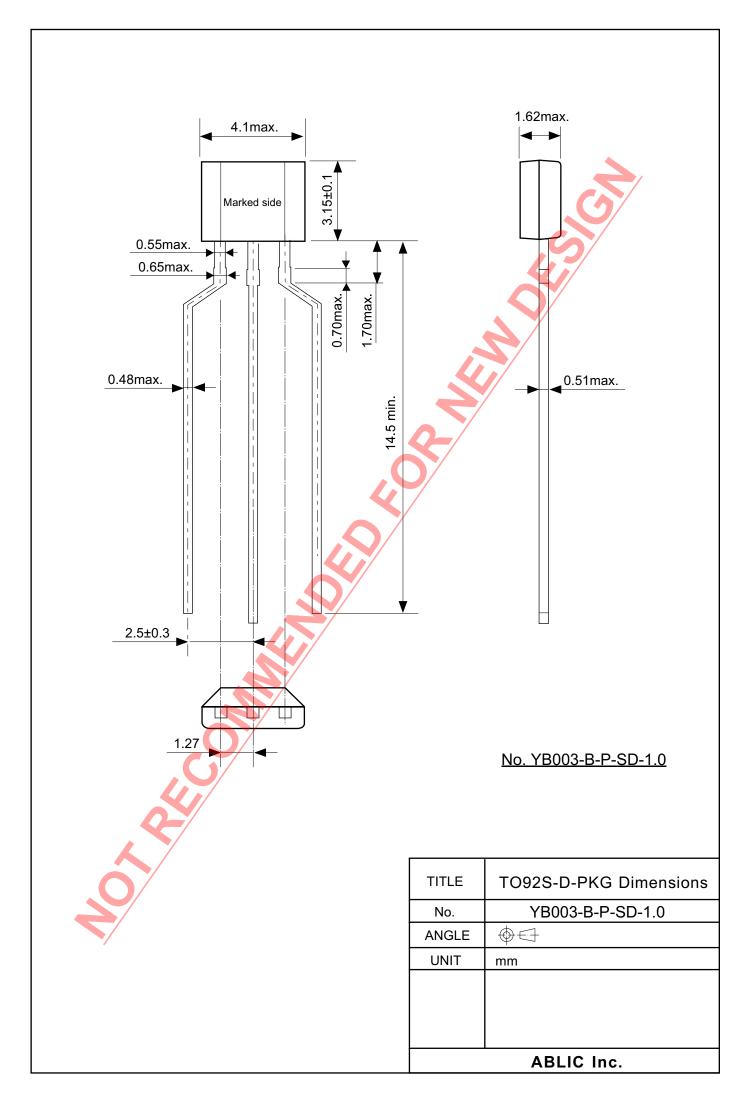
### **TO-92S**

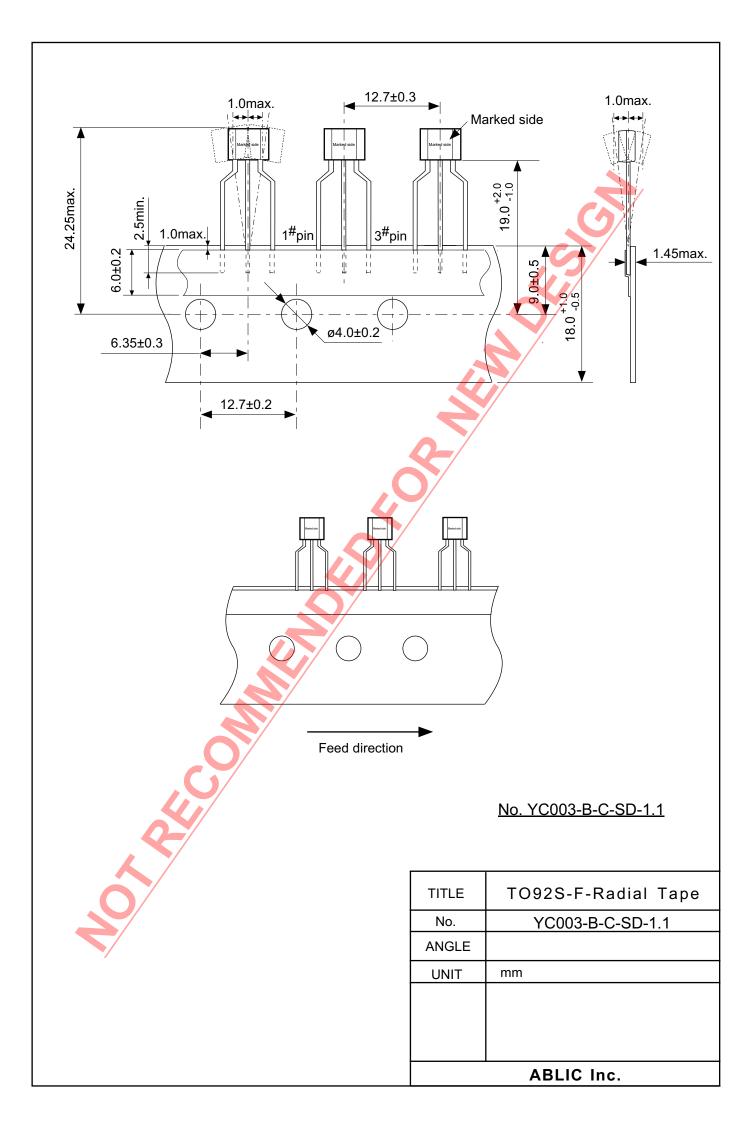


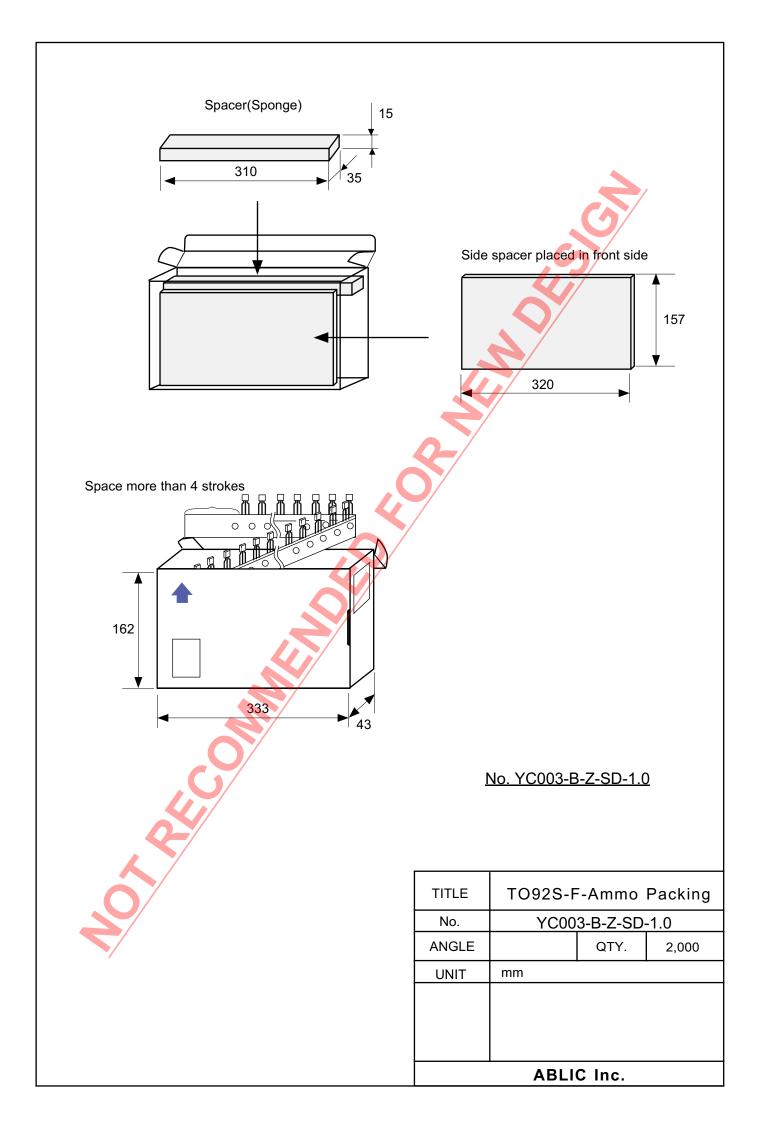












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